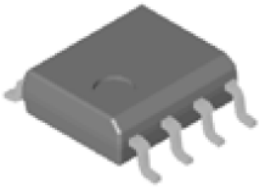
P & N-Channel 20-V (D-S) MOSFET

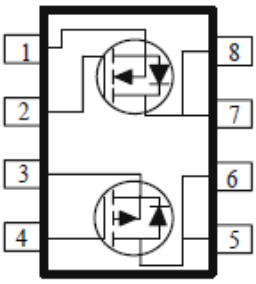
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (mΩ)	I_D(A)
20	47 @ V_{GS} = 4.5V	6.6
	55 @ V_{GS} = 2.5V	6.2
-20	79 @ V_{GS} = -4.5V	-5.2
	110 @ V_{GS} = -2.5V	-4.4

Key Features:
- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

Typical Applications:
- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

Pb-free
RoHS COMPLIANT
HALOGEN FREE





ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		**Symbol**	**Nch Limit**	**Pch Limit**	**Units**
Drain-Source Voltage		V_{DS}	20	-20	V
Gate-Source Voltage		V_{GS}	±8	±8	
Continuous Drain Current [a]	T_A=25°C	I_D	6.6	-5.2	A
	T_A=70°C		5	-3.8	
Pulsed Drain Current [b]		I_{DM}	20	-20	
Continuous Source Current (Diode Conduction) [a]		I_S	2.2	-2.2	A
Power Dissipation [a]	T_A=25°C	P_D	2.1	2.1	W
	T_A=70°C		1.3	1.3	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		°C

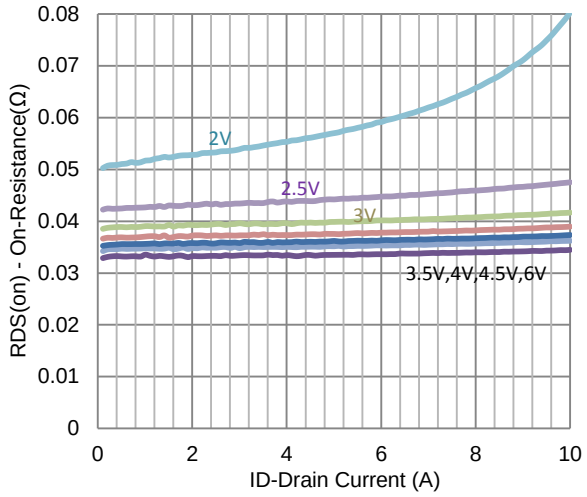
THERMAL RESISTANCE RATINGS				
Parameter		**Symbol**	**Maximum**	**Units**
Maximum Junction-to-Ambient [a]	t <= 10 sec	$R_{\theta JA}$	62.5	°C/W
	Steady State		110	

Notes
a. Surface Mounted on 1” x 1” FR4 Board.
b. Pulse width limited by maximum junction temperature

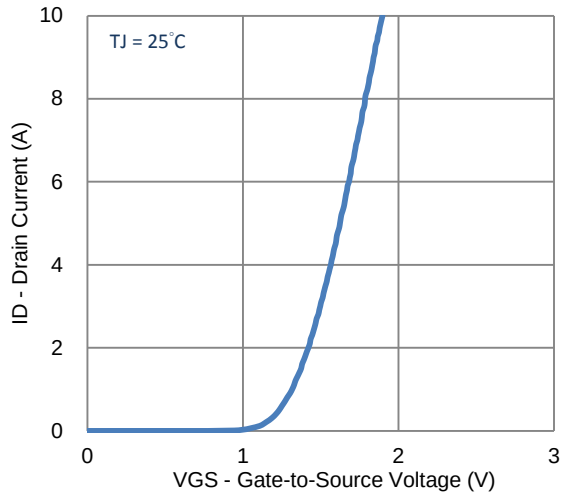
Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 uA **(N-ch)**	1			V
		V_{DS} = V_{GS}, I_D = -250 uA **(P-ch)**	-1			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 8 V, V_{GS} = 0 V **(N-ch)**			1	uA
		V_{DS} = -8 V, V_{GS} = 0 V **(P-ch)**			-1	
On-State Drain Current	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 4.5 V **(N-ch)**	10			A
		V_{DS} = -5 V, V_{GS} = -4.5 V **(P-ch)**	-10			A
Drain-Source On-Resistance	$r_{DS(on)}$	V_{GS} = 4.5 V, I_D = 5.3 A **(N-ch)**			47	mΩ
		V_{GS} = 2.5 V, I_D = 5 A **(N-ch)**			55	
		V_{GS} = -4.5 V, I_D = -4.2 A **(P-ch)**			79	mΩ
		V_{GS} = -2.5 V, I_D = -3.8 A **(P-ch)**			110	
Forward Transconductance	g_{fs}	V_{DS} = 10 V, I_D = 5.3 A **(N-ch)**		10		S
		V_{DS} = -10 V, I_D = -4.2 A **(P-ch)**		10		S
Diode Forward Voltage	V_{SD}	I_S = 1.1 A, V_{GS} = 0 V **(N-ch)**		0.7		V
		I_S = -1.1 A, V_{GS} = 0 V **(P-ch)**		-0.73		V
Dynamic						
Total Gate Charge	Q_g	N - Channel V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 5.3 A		6		nC
Gate-Source Charge	Q_{gs}			0.9		
Gate-Drain Charge	Q_{gd}			2.1		
Turn-On Delay Time	$t_{d(on)}$	N - Channel V_{DD} = 10 V, R_L = 1.8 Ω, I_D = 5.3 A, V_{GEN} = 4.5 V, R_{GEN} = 6 Ω		7		ns
Rise Time	t_r			24		
Turn-Off Delay Time	$t_{d(off)}$			35		
Fall Time	t_f			19		
Input Capacitance	C_{iss}	N - Channel V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		439		pF
Output Capacitance	C_{oss}			78		
Reverse Transfer Capacitance	C_{rss}			68		
Total Gate Charge	Q_g	P - Channel V_{DS} = -10 V, V_{GS} = 4.5 V, I_D = -4.2 A		11		nC
Gate-Source Charge	Q_{gs}			2.8		
Gate-Drain Charge	Q_{gd}			2.7		
Turn-On Delay Time	$t_{d(on)}$	P - Channel V_{DD} = -10 V, R_L = 2.3 Ω, I_D = -4.2 A, V_{GEN} = -4.5 V, R_{GEN} = 6 Ω		10		ns
Rise Time	t_r			20		
Turn-Off Delay Time	$t_{d(off)}$			49		
Fall Time	t_f			21		
Input Capacitance	C_{iss}	P - Channel V_{DS} = -15 V, V_{GS} = 0 V, f = 1 MHz		683		pF
Output Capacitance	C_{oss}			90		
Reverse Transfer Capacitance	C_{rss}			75		

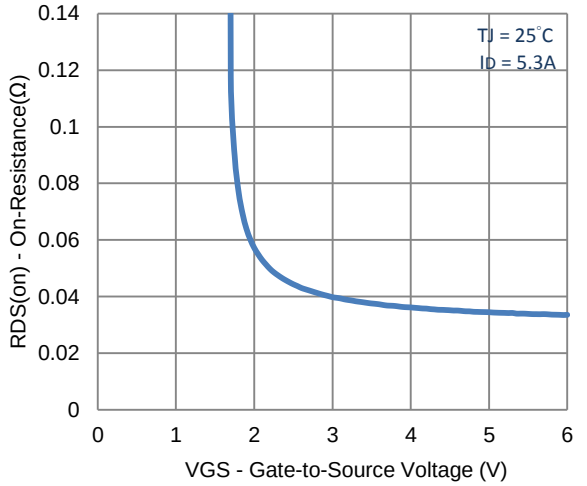
Typical Electrical Characteristics - N-channel



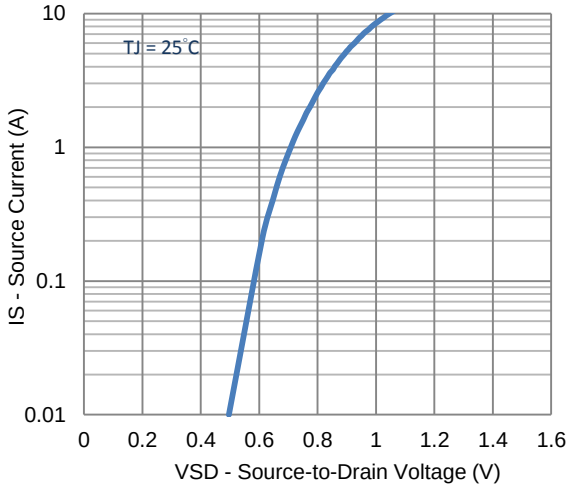
1. On-Resistance vs. Drain Current



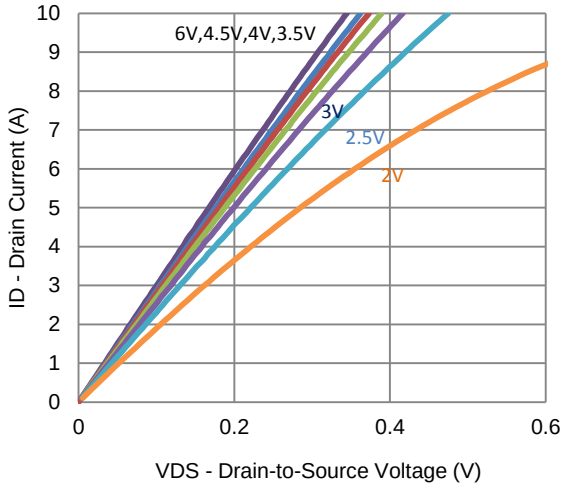
2. Transfer Characteristics



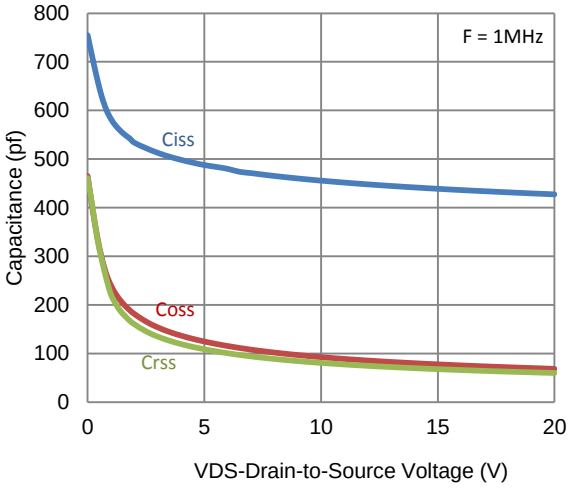
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage

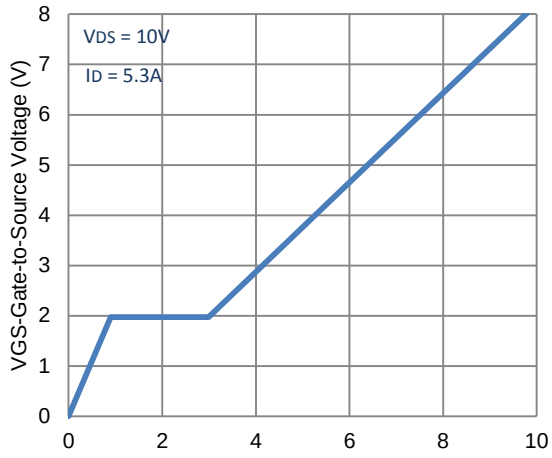


5. Output Characteristics

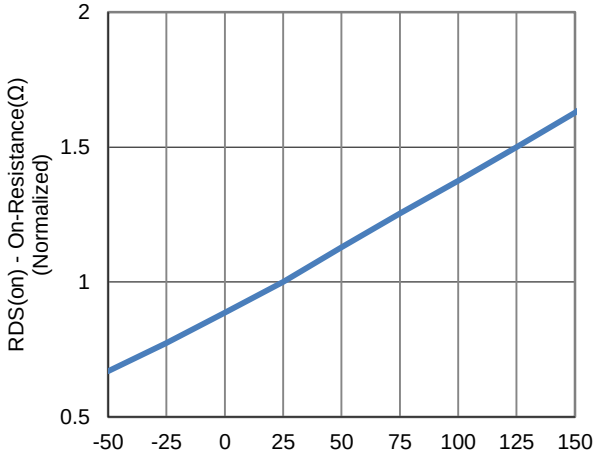


6. Capacitance

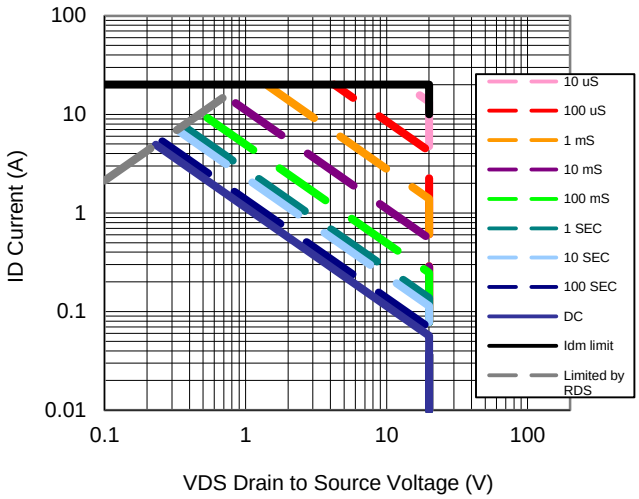
Typical Electrical Characteristics - N-channel



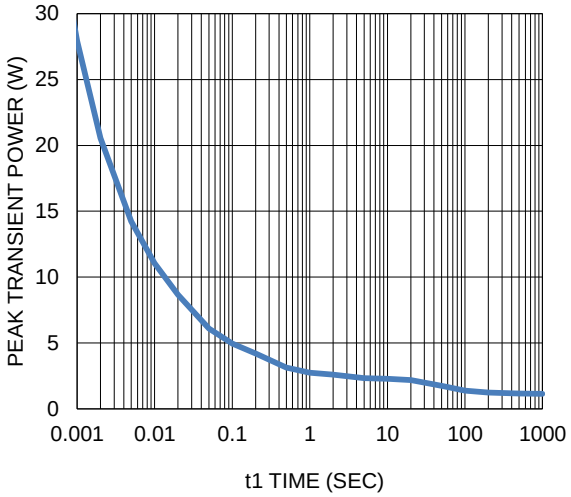
7. Gate Charge



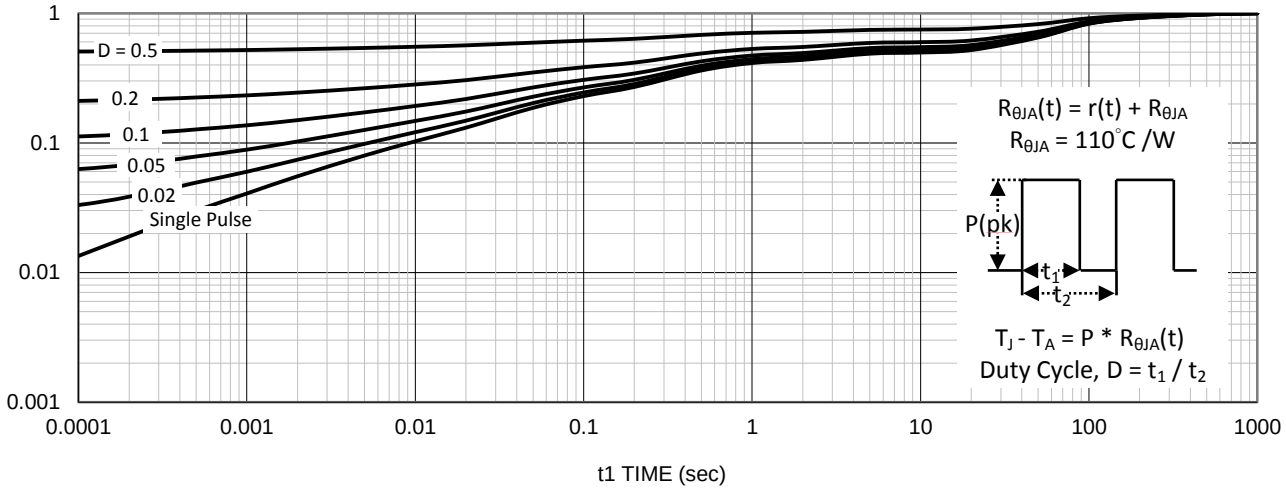
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

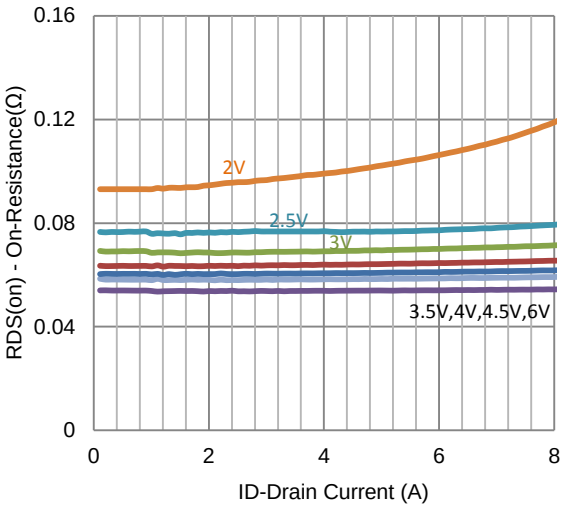


10. Single Pulse Maximum Power Dissipation

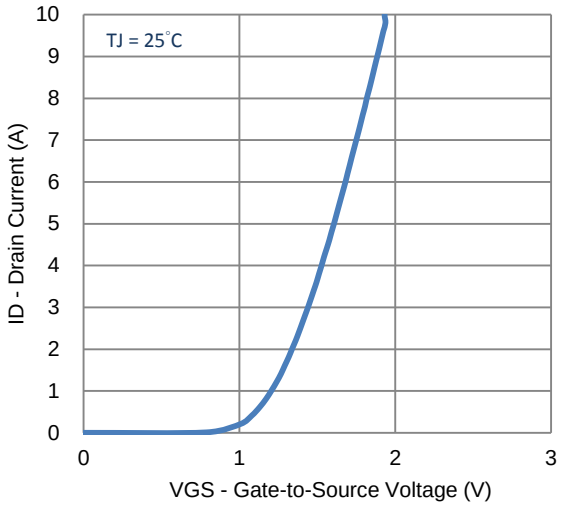


11. Normalized Thermal Transient Junction to Ambient

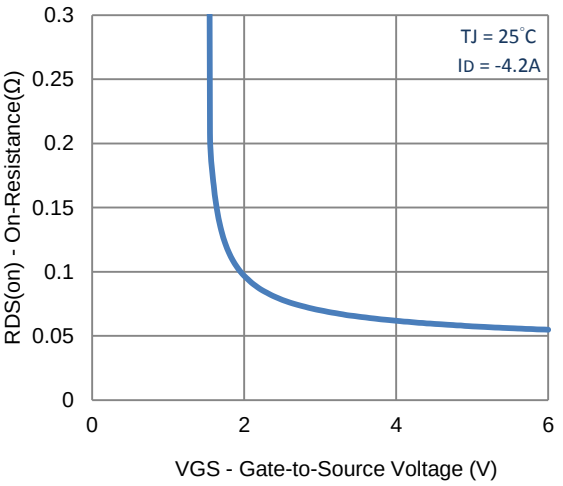
Typical Electrical Characteristics - P-channel



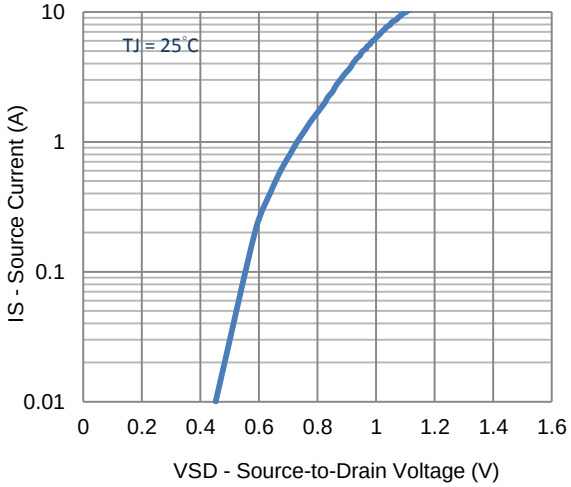
1. On-Resistance vs. Drain Current



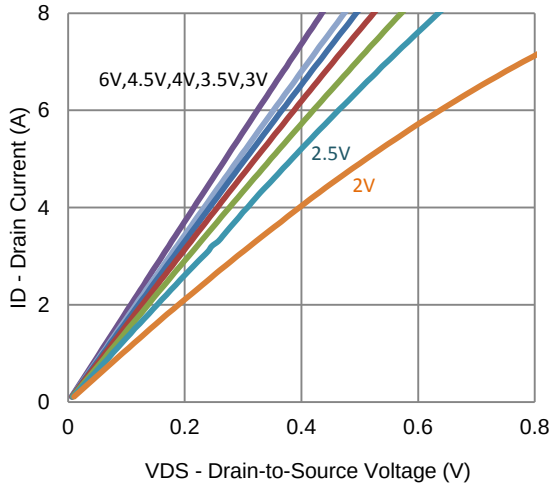
2. Transfer Characteristics



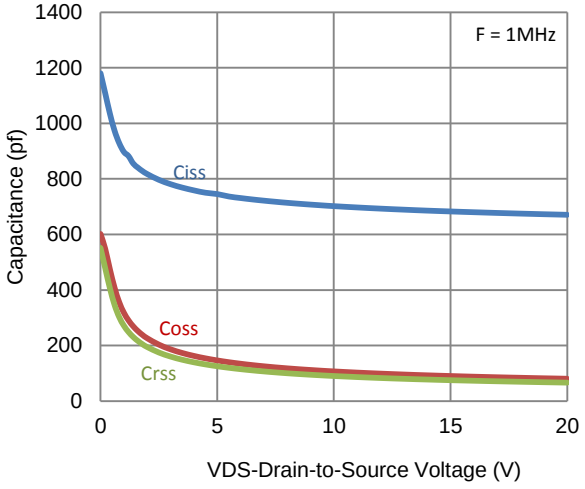
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage

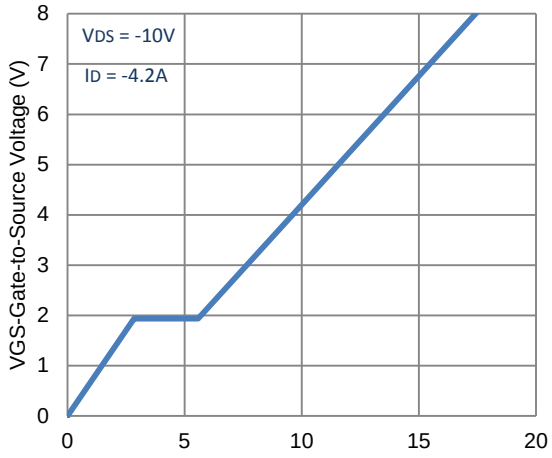


5. Output Characteristics

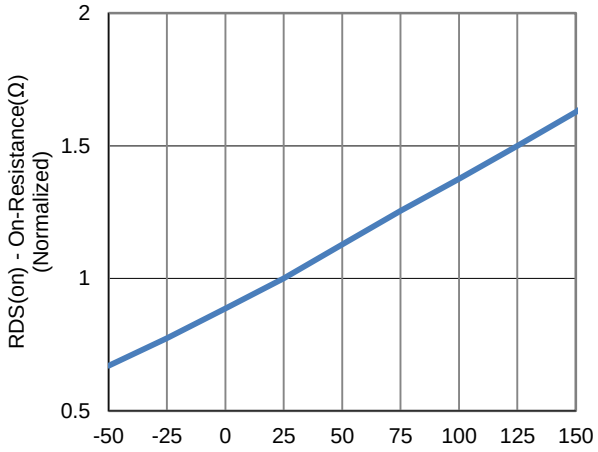


6. Capacitance

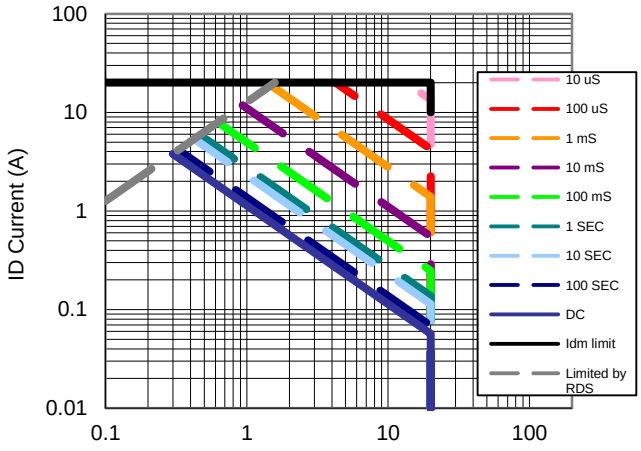
Typical Electrical Characteristics - P-channel



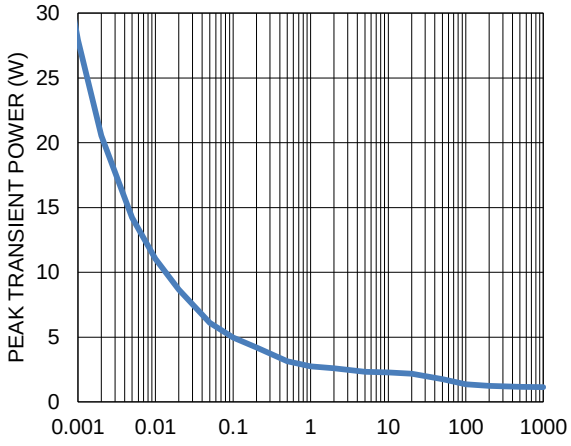
7. Gate Charge



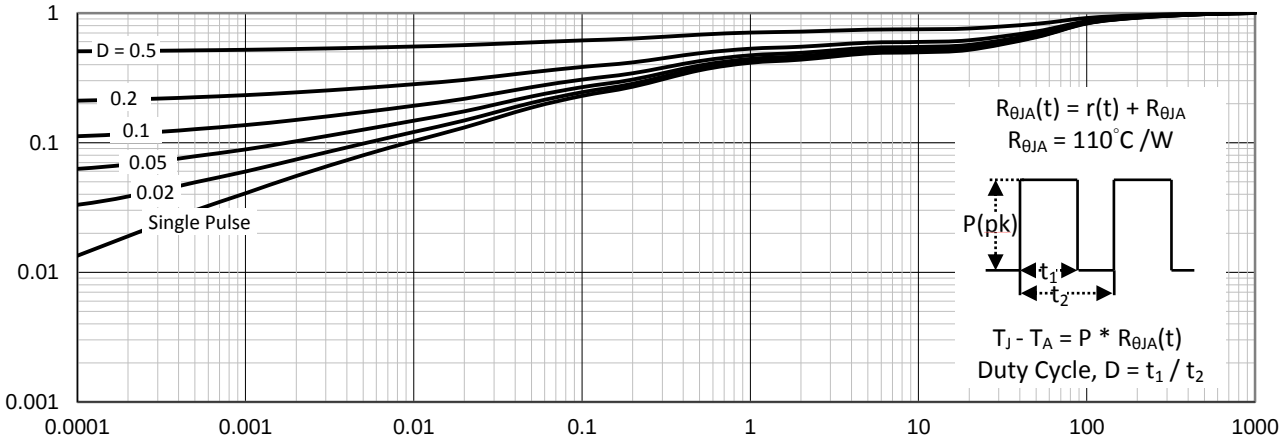
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area



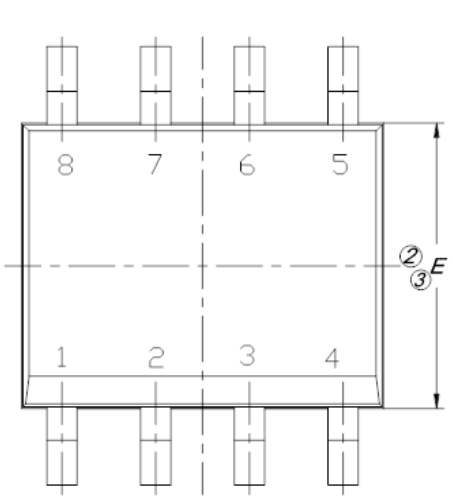
10. Single Pulse Maximum Power Dissipation

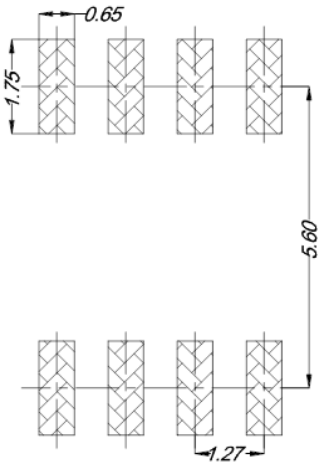


11. Normalized Thermal Transient Junction to Ambient

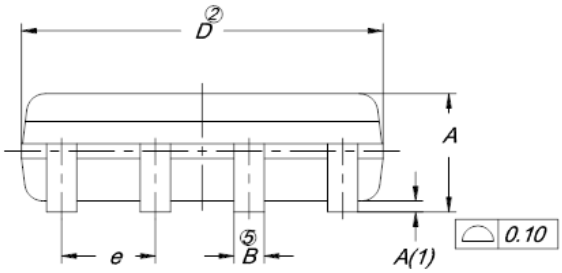
Package Information

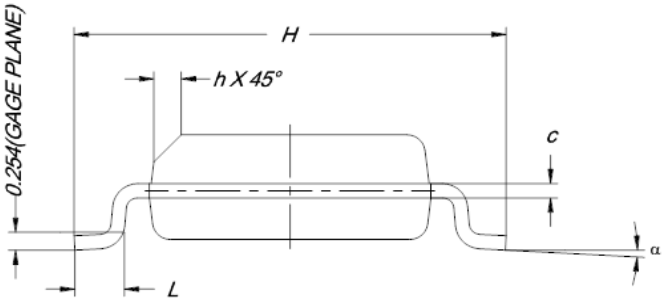
Land Pattern
(Only for Reference)





DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.35	1.55	1.75
A(1)	0.10	0.18	0.25
B	0.38	0.45	0.51
C	0.19	0.22	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
e	1.27 BSC		
H	5.80	6.00	6.20
L	0.50	0.72	0.93
α	0°	4°	8°
h	0.25	0.38	0.50





Note:
1. All Dimension Are In mm.
2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
4. The Package Top May Be Smaller Than The Package Bottom.
5. Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.